

# Benjamin A. D. Williamson MSci, PhD, MRSC, NKS

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## Employment

### Norwegian University of Science and Technology (NTNU) (2019 – Present)

Postdoctoral Researcher in Computational Materials Design  
Functional Materials and Materials Chemistry Research Group (FACET)  
Advisor: Prof. Sverre M. Selbach

### University College London (2018 – 2019)

Postdoctoral Research Associate in Computational Materials Design  
Scanlon Materials Theory Group  
Advisor: Prof. David O. Scanlon

## Education

### University College London (2014 – 2018)

PhD in Computational Inorganic Materials Chemistry  
Thesis title : *Understanding the Electronic and Thermodynamic Properties of Wide Band Gap Materials*  
Supervisor: Prof. David O. Scanlon; Secondary Supervisor: Prof. Claire J. Carmalt

### University College London (2010 – 2014)

MSci in Chemistry – 1<sup>st</sup> Class Honours  
MSci dissertation title: *Computational Design of Next-Generation p-Type Semiconductors*  
Supervisor: Prof. David O. Scanlon

## Publications

1. *Resonant Ta Doping for Enhanced Mobility in Transparent Conducting SnO<sub>2</sub>*  
**B.A.D. Williamson**, T.J. Featherstone, S. Sathasivam, J.E.N. Swallow, H. Shiel, L.A.H. Jones, M.J. Smiles, A. Regoutz, T.-L. Lee, X. Xia, C. Blackman, P.K. Thakur, C.J. Carmalt, I.P. Parkin, T.D. Veal and D.O. Scanlon; *ChemRxiv* (2018)  
DOI: 10.26434/chemrxiv.10561145
2. *Resonant Doping for High Mobility Transparent Conductors: The Case of Mo-doped In<sub>2</sub>O<sub>3</sub>*  
J.E.N. Swallow, **B.A.D. Williamson**, S. Sathasivam, M. Birkett, T.J. Featherstone, P.A.E. Murgatroyd, H.J. Edwards, Z.W. Lebens-Higgins, D.A. Duncan, M. Farnworth, P. Warren, N. Peng, T.-L. Lee, L.F.J. Piper, A. Regoutz, C.J. Carmalt, I.P. Parkin, V.R. Dhanak, D.O. Scanlon and T.D. Veal; *Mater. Horiz., Advance Article*, (2019)  
DOI: 10.1039/C9MH01014A
3. *Dispelling the Myth of Passivated Codoping in TiO<sub>2</sub>*  
**B.A.D. Williamson**, J. Buckeridge, N.P. Chadwick, S. Sathasivam, C.J. Carmalt, I.P. Parkin and D.O. Scanlon; *Chem. Mater.*, 31 (7), 2577-2589 (2019)  
DOI: 10.1021/acs.chemmater.9b00257
4. *Computationally Driven Discovery of Layered Quinary Oxychalcogenides: Potential p-Type Transparent Conductors?*  
**B.A.D. Williamson**, G.J. Limburn, G. Hyett and D.O. Scanlon; *ChemRxiv* (2018)  
DOI: 10.26434/chemrxiv.7078205
5. *Origin of High-Efficiency Photoelectrochemical Water Splitting on Hematite/Functional Nanohybrid Metal Oxide Overlayer Photoanode after a Low Temperature Inert Gas Annealing Treatment*  
S. Ho-Kimura, **B.A.D. Williamson**, S. Sathasivam, S.J.A. Moniz, G. He, W. Luo, D.O. Scanlon, J. Tang, I.P.

Parkin; *ACS Omega*, 4 (1), 1449-1459 (2019)

DOI: 10.1021/acsomega.8b02444

6. *Phosphorus Doped SnO<sub>2</sub> Thin Films for Transparent Conducting Oxide Applications: Synthesis, Optoelectronic Properties and Computational Models*  
M.J. Powell, **B.A.D. Williamson**, S-Y. Baek, J. Manzi, D. Potter, D.O. Scanlon and C.J. Carmalt; *Chem. Sci.*, 9 (4), 7968-7980 (2018)  
DOI: 10.1039/C8SC02152J
7. *Enhanced Electrical Properties of Antimony Doped Tin Oxide Thin Films Deposited via Aerosol Assisted Chemical Vapour Deposition*  
S. Ponja, **B.A.D. Williamson**, S. Sathasivam, D.O. Scanlon, I.P. Parkin, C.J. Carmalt; *J. Mater. Chem. C*, 6, 7257-7266 (2018)  
DOI: 10.1039/C8TC01929K
8. *A Novel Laboratory-based Hard X-ray Photoelectron Spectroscopy System*  
A. Regoutz, M. Mascheck, T. Wiell, S.K. Eriksson, C. Liljenberg, K. Tetzner, **B.A.D. Williamson**, D. O. Scanlon and P. Palmgren; *Rev. Sci. Instr.*, 89 (7), 073105 (2018)  
DOI: 10.1063/1.5039829
9. *Chemical Vapor Deposition of Photocatalytically Active Pure Brookite TiO<sub>2</sub> Thin Films*  
A.M. Alotaibi, S. Sathasivam, **B.A.D. Williamson**, A. Kafizas, C. Sotelo-Vazquez, A. Taylor, D.O. Scanlon, and I.P. Parkin; *Chem. Mater.*, 30 (4), 1353-1361 (2018)  
DOI: 10.1021/acs.chemmater.7b04944
10. *A Deeper Understanding of Interstitial Boron-Doped Anatase Thin Films as A Multifunctional Layer Through Theory and Experiment*  
M. Quesada-Gonzalez, **B.A.D. Williamson**, C. Sotelo-Vazquez, A. Kafizas, N.D. Boscher, R. Quesada-Cabrera, D.O. Scanlon, C.J. Carmalt, I.P. Parkin; *J. Phys. Chem. C*, 122 (1), 714-726 (2018)  
DOI: 10.1021/acs.jpcc.7b11142
11. *Self-Compensation in Transparent Conducting F-Doped SnO<sub>2</sub>*  
J.E.N. Swallow, **B.A.D. Williamson**, T.J. Whittles, M. Birkett, T.J. Featherstone, N. Peng, A. Abbott, M. Farnworth, K.J. Cheetham, P. Warren, D.O. Scanlon, V.R. Dhanak, T.D. Veal; *Adv. Funct. Mater.*, 1701900 (2017)  
DOI: 10.1002/adfm.201701900
12. *Chemical Vapor Deposition Synthesis and Optical Properties of Nb<sub>2</sub>O<sub>5</sub> Thin Films with Hybrid Functional Theoretical Insight into Band Structure and Band Gaps*  
S. Sathasivam, **B.A.D. Williamson**, S.A. Al Thabaiti, A.Y. Obaid, S.N. Basahel, M. Mokhtar, D.O. Scanlon, C.J. Carmalt, I.P. Parkin; *ACS Appl. Mater. Interfaces*, 9 (21), 18031-18038 (2017)  
DOI: 10.1021/acsami.7b00907
13. *Computational and Experimental Study of Ta<sub>2</sub>O<sub>5</sub> Thin Films*  
S. Sathasivam, **B.A.D. Williamson**, A. Kafizas, S.A. Althabaiti, A.Y. Obaid, S.N. Basahel, D.O. Scanlon, C.J. Carmalt, I.P. Parkin; *J. Phys. Chem. C*, 121 (1), 202-210 (2017)  
DOI: 10.1021/acs.jpcc.6b11073
14. *Transparent Conducting n-type ZnO:Sc – Synthesis, Optoelectronic Properties and Theoretical Insight*  
S.C. Dixon, S. Sathasivam, **B.A.D. Williamson**, D.O. Scanlon, C.J. Carmalt, I.P. Parkin; *J. Mater. Chem. C*, 5, 7585-7597 (2017)  
DOI: 10.1039/C7TC02389H
15. *Engineering Valence Band Dispersion for High Mobility p-Type Semiconductors*  
**B.A.D. Williamson**, J. Buckeridge, J. Brown, S. Ansbro, R.G. Palgrave, D.O. Scanlon; *Chem. Mater.*, 29 (6), 2402-2413 (2017)  
DOI: 10.1021/acs.chemmater.6b03306

16. *A Single-Source Precursor Approach to Solution Processed Indium Arsenide Thin Films*  
P. Marchand, S. Sathasivam, **B.A.D. Williamson**, D. Pugh, S.M. Bawaked, S.N. Basahel, A.Y. Obaid, D.O. Scanlon, I.P. Parkin, C.J. Carmalt; *J. Mater. Chem. C*, 4, 6761-6768 (2016)  
DOI: 10.1039/C6TC02293F

## Conference Presentations

1. Contributed: B.A.D Williamson: *Resonant Doping for High Mobility Transparent Conductors: The Case of Mo-doped  $\text{In}_2\text{O}_3$* , 11th Petite Workshop on defects in energy materials; Sommarøy, Norway 2019 – Oral
2. Contributed: B.A.D Williamson: *Computationally Aided Discovery of Layered Quinary Oxychalcogenide p-type Transparent Conductor*, Workshop For Atomistic Modelling; Trondheim, Norway 2019 – Poster
3. Contributed: B.A.D Williamson: *Dispelling the Myth of Passivated Codoping in  $\text{TiO}_2$* , MRS Fall Meeting; Boston US, 2018 – Oral
4. Contributed: B.A.D. Williamson: *Computationally Aided Discovery of Layered Quinary Oxychalcogenide p-type Transparent Conductors*, MRS Fall Meeting; Boston US, 2018 – Poster  
**Winner of the ICDD prize for materials characterisation**
5. Contributed: B.A.D Williamson: *Doubled Conductivity in Transparent Conducting  $\text{In}_2\text{O}_3$  Through Novel Dopant Design*, MMM Hub; Thomas Young Centre, London, UK, 2018 – Poster
6. Invited: B.A.D Williamson: *Doubled Conductivity in Transparent Conducting  $\text{In}_2\text{O}_3$  Through Novel Dopant Design*, MCC 3rd Conference, Lincoln UK, 2018 – Oral
7. Contributed: B.A.D Williamson: *Doubled Conductivity in Transparent Conducting  $\text{In}_2\text{O}_3$  Through Novel Dopant Design*, Gordon Research Conference; Defects In Semiconductors, Colby-Sawyer College, New Hampshire, US, 2018 – Poster
8. Invited: B.A.D Williamson: *Beyond Conventional Doping in  $\text{SnO}_2$* , Thomas Young Centre, London UK, 2017 – Oral
9. Contributed: B.A.D Williamson: *Beyond Conventional Doping in  $\text{SnO}_2$* , E-MRS; Spring Meeting, Strasbourg France, 2017 – Poster
10. Contributed: B.A.D Williamson: *Engineering Valence Band Dispersion For High-Mobility p-type Semiconductors*, E-MRS; Spring Meeting, Strasbourg France, 2017 – Oral
11. Contributed: B.A.D Williamson: *Engineering Valence Band Dispersion For High-Mobility p-type Semiconductors*, MRS Fall Meeting; Boston US, 2016 – Poster
12. Contributed: B.A.D Williamson: *Engineering Valence Band Dispersion For High-Mobility p-type Semiconductors*, SSCG Christmas Meeting; Canterbury UK, 2015 – Poster

## Teaching

2014 – 2019: Supervised six final year MSci research projects at UCL  
2014 – 2019: Demonstrated in 1<sup>st</sup> year undergraduate workshops (CHEM1004)  
2018 – 2019: Tutor in 1<sup>st</sup> year undergraduate inorganic chemistry courses at UCL (CHEM1101 and CHEM0013)

## References

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